

100V, 4A, High Frequency Half-Bridge Gate Driver

DESCRIPTION

The MP1924 is a high-frequency, 100V, half-bridge, N-channel, power MOSFET driver. Its low-side and high-side driver channels are independently controlled and matched with less than 5ns in time delay. Under-voltage lockout on both high-side and low-side supplies force their outputs low in case of insufficient supply. The integrated bootstrap diode reduces external component count.

FEATURES

- Drives an N-Channel MOSFET Half Bridge
- 118V V_{BST} Voltage Range
- On-Chip Bootstrap Diode
- Typical Propagation Delay of 20ns
- Gate Drive Matching of Less than 5ns
- Drives a 2.2nF Load with 15ns Rise Time and 12ns Fall Time at 12V VDD
- TTL-Compatible Input
- Quiescent Current of Less than 150μA
- UVLO for Both High Side and Low Side
- QFN-10 (4mmx4mm) and SOIC-8 Packages

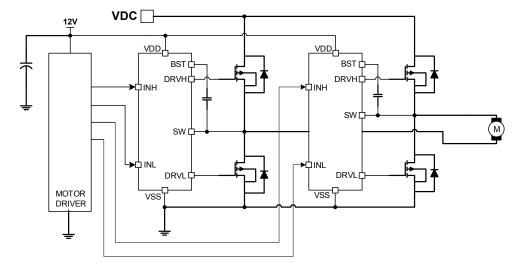
APPLICATIONS

- Motor Drivers
- Telecom Half-Bridge Power Supplies
- Avionics DC-DC Converters
- Two-Switch Forward Converters
- Active-Clamp Forward Converters

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TYPICAL APPLICATION





ORDERING INFORMATION

Part Number	Package	Top Marking
MP1924HR*	QFN-10 (4x4mm)	See Below
MP1924HS**	SOIC-8	See Below

* For Tape & Reel, add suffix –Z (e.g. MP1924HR–Z)
For RoHS compliant packaging, add suffix –LF (e.g. MP1924HR–LF–Z)

** For Tape & Reel, add suffix –Z (e.g. MP1924HS–Z)
For RoHS compliant packaging, add suffix –LF (e.g. MP1924HS–LF–Z)

TOP MARKING (MP1924HR)

<u>MPSYWW</u> MP1924 LLLLLL

MPS: MPS prefix; Y: year code; WW: week code;

MP1924: product code of MP1924HR;

LLLLLL: lot number;

TOP MARKING (MP1924HS)

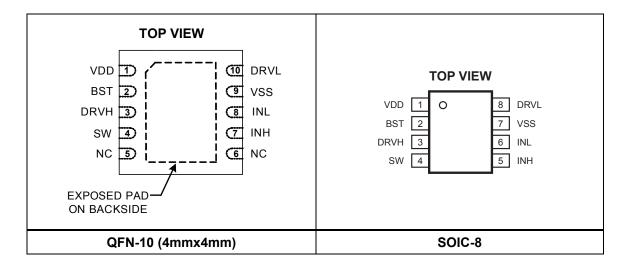
MP1924 LLLLLLLL MPSYWW

MP1924: product code of MP1924HS;

LLLLLLL: lot number; MPS: MPS prefix; Y: year code; WW: week code;



PACKAGE REFERENCE



ABSOLUTE MAXIMUM RATINGS (1)

Supply Voltage (V _{DD})	0.3V to 18V
SW Voltage (V _{SW})	5.0V to 105V
BST Voltage (V _{BST})	0.3V to 118V
BST to SW	0.3V to 18V
DRVH to SW0.3V to (E	3ST-SW) + 0.3V
DRVL to VSS0.3V	to (VDD + 0.3V)
All Other Pins0.3\	$/ \text{ to } (V_{DD} + 0.3V)$
Continuous Power Dissipation	$(T_A = 25^{\circ}C)^{(2)}$
QFN-10 (4mmx4mm)	2.66W
SOIC-8	1.3W
Junction Temperature	150°C
Lead Temperature	260°C
Storage Temperature	-65°C to 150°C

Recommended Operating Conditions (3)

Supply Voltage V _{DD}	9.0V to 16.0V
SW Voltage (V _{SW})	1.0V to 100V
SW Slew Rate	<50V/ns
Operating Junction Temp. (7	「」)40°C to 125°C

Thermal Resistance (4)	$oldsymbol{ heta}_{JA}$	$oldsymbol{ heta}_{JC}$	
QFN-10 (4mmx4mm)	47	7	.°C/W
SOIC-8	96	45	.°C/W

Notes:

- 1) Exceeding these ratings may damage the device.
- 2) The maximum allowable power dissipation is a function of the maximum junction temperature $T_J(MAX),$ the junction-to-ambient thermal resistance $\theta_{JA},$ and the ambient temperature $T_A.$ The maximum allowable continuous power dissipation at any ambient temperature is calculated by $P_D(MAX)=(T_J(MAX)-T_A)/\theta_{JA}.$ Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- The device is not guaranteed to function outside of its operating conditions.
- 4) Measured on JESD51-7, 4-layer PCB.



ELECTRICAL CHARACTERISTICS

 V_{DD} = V_{BST} - V_{SW} = 12V, V_{SS} = V_{SW} = 0V, No load at DRVH and DRVL, T_A = +25°C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units	
Supply Currents							
VDD quiescent current	I_{DDQ}	INL = INH = 0		100	150	μΑ	
VDD operating current	I _{DDO}	fsw = 500kHz		9		mA	
Floating driver quiescent current	I_{BSTQ}	INL = INH = 0		60	90	μA	
Floating driver operating current	I _{BSTO}	fsw = 500kHz		7.5		mA	
Leakage current	I_{LK}	BST = SW = 100V		0.05	1	μА	
Inputs							
INL/INH High				2	2.4	V	
INL/INH Low			1	1.4		V	
INL/INH internal pull-down	R _{IN}			185		kΩ	
resistance	IXIN			100		NS 2	
Under Voltage Protection							
VDD rising threshold	V_{DDR}		8.1	8.4	8.8	V	
VDD hysteresis	V_{DDH}			0.5		V	
(BST-SW) rising threshold	V_{BSTR}		6.9	7.3	7.7	V	
(BST-SW) hysteresis	V_{BSTH}			0.55		V	
Bootstrap Diode							
Bootstrap diode VF @ 100µA	V_{F1}			0.5		V	
Bootstrap diode VF @ 100mA	V _{F2}			0.95		V	
Bootstrap diode dynamic R	R_{D}	@ 100mA		2		Ω	
Low Side Gate Driver							
Low level output voltage	V _{OLL}	I _O = 100mA		0.08		V	
High level output voltage to rail	V_{OHL}	I _O = -100mA		0.23		V	
Source Current ⁽⁵⁾	I _{OHL}	$V_{DRVL} = 0V, V_{DD} = 12V$		3		Α	
Source Current		$V_{DRVL} = 0V, V_{DD} = 16V$		4.7		Α	
Sink Current ⁽⁵⁾	1	$V_{DRVL} = V_{DD} = 12V$		4.5		Α	
Sink Current	I _{OLL}	$V_{DRVL} = V_{DD} = 16V$		6		Α	
Floating Gate Driver							
Low level output voltage	V_{OLH}	I _O = 100mA		0.08		V	
High level output voltage to rail	V _{OHH}	I _O = -100mA		0.23		V	
Source Current ⁽⁵⁾		$V_{DRVH} = 0V, V_{DD} = 12V$		2.6		Α	
Source Current	I _{OHH}	$V_{DRVH} = 0V$, $V_{DD} = 16V$		4		Α	
Sink Current ⁽⁵⁾	ı	$V_{DRVH} = V_{DD} = 12V$		4.5		Α	
Sink Current ''	I _{OLH}	$V_{DRVH} = V_{DD} = 16V$		5.9		Α	



ELECTRICAL CHARACTERISTICS (continued)

 V_{DD} = V_{BST} - V_{SW} = 12V, V_{SS} = V_{SW} = 0V, No load at DRVH and DRVL, T_A = +25°C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
Switching Spec Low Side Gate Driver						
Turn-off propagation delay INL falling to DRVL falling	T_{DLFF}			20		ns
Turn-on propagation delay INL rising to DRVL rising	T _{DLRR}			20		
DRVL rise time		$C_L = 2.2nF$		15		ns
DRVL fall time		$C_L = 2.2nF$		9		ns
Switching Spec Floating Gate	e Driver					
Furn-off propagation delay NH falling to DRVH falling				20		ns
Turn-on propagation delay INH rising to DRVH rising	T _{DHRR}			20		ns
DRVH rise time		$C_L = 2.2nF$		15		ns
DRVH fall time		$C_L = 2.2nF$		12		ns
Switching Spec Matching						
Floating driver turn-off to low side drive turn-on ⁽⁵⁾	T _{MON}			1	5	ns
Low side driver turn-off to floating driver turn-on ⁽⁵⁾	T _{MOFF}			1	5	ns
Minimum input pulse width that changes the output $^{(5)}$					50	ns
Bootstrap diode turn-on or turn-off time ⁽⁵⁾	Bootstrap diode turn-on or turn- off time ⁽⁵⁾			10		ns
Thermal shutdown				150		°C
Thermal shutdown hysteresis				25		°C

Note:

⁵⁾ Guaranteed by design.

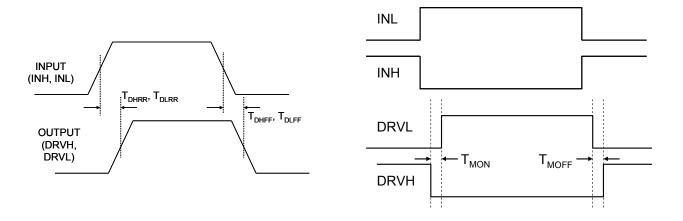


Figure 1: Timing Diagram



PIN FUNCTIONS

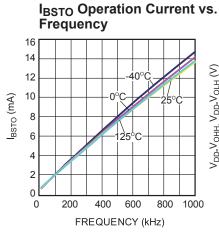
QFN4x4-10 Pin #	SOIC-8 Pin#	Name	Description
1	1	VDD	Supply input. This pin supplies power to all the internal circuitry. Place a decoupling capacitor to ground close to this pin to ensure stable and clean supply.
2	2	BST	Bootstrap. This is the positive power supply for the internal floating high-side MOSFET driver. Connect a bypass capacitor between this pin and SW pin.
3	3	DRVH	Floating driver output.
4	4	SW	Switching node.
5, 6		NC	No connection.
7	5	INH	Control signal input for the floating driver.
8	6	INL	Control signal input for the low side driver.
9	7	VSS, exposed pad	Chip ground. Connect exposed pad to VSS for proper thermal operation.
10	8	DRVL	Low side driver output.

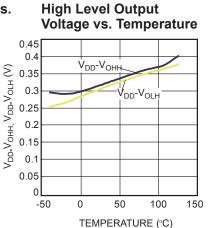


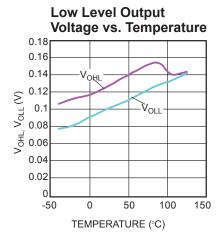
TYPICAL PERFORMANCE CHARACTERISTICS

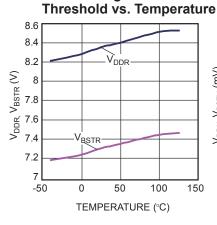
 V_{DD} =12V, V_{SS} = V_{SW} = 0V, T_A = +25°C, unless otherwise noted.

I_{DDO} Operation Current vs. Frequency 20 18 16 -40°C 14 l_{DDO} (mA) 12 10 25°C 6 25°C 0 800 400 600 FREQUENCY (kHz)

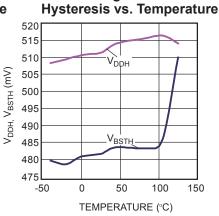




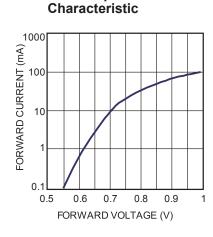




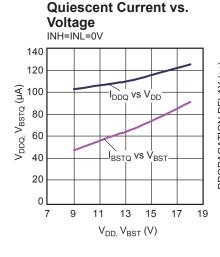
Undervoltage Lockout

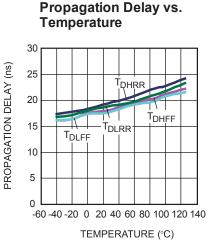


Undervoltage Lockout



Bootstrap Diode I-V



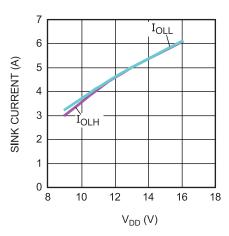




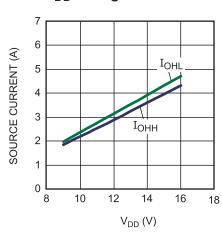
TYPICAL PERFORMANCE CHARACTERISTICS (continued)

 V_{DD} =12V, V_{SS} = V_{SW} = 0V, T_A = +25°C, unless otherwise noted.

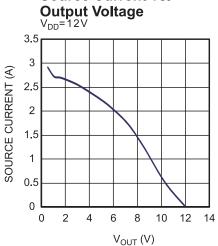
Sink Current vs. **V_{DD}** Voltage



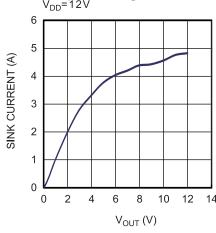
Source Current vs. **V_{DD}** Voltage



Source Current vs.



Sink Current vs. Output Voltage



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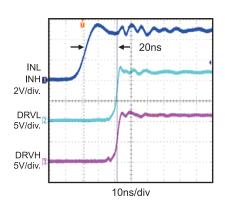
TYPICAL PERFORMANCE CHARACTERISTICS (continued)

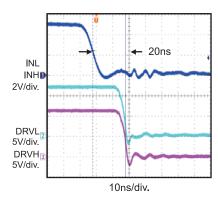
 V_{DD} =12V, V_{SS} = V_{SW} = 0V, T_A = +25°C, unless otherwise noted.

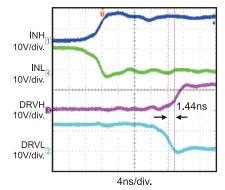
Turn-on Propagation Delay

Turn-off Propagation Delay

Gate Drive Matching T_{MOFF}



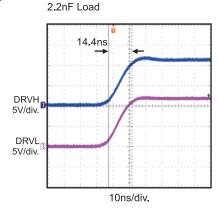




Gate Drive Matching T_{MON}

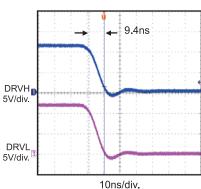
INH 10V/div. INL 10V/div. DRVH 10V/div. DRVL 10V/div. 4ns/div.

Drive Rise Time



Drive Fall Time

2.2nF Load





BLOCK DIAGRAM

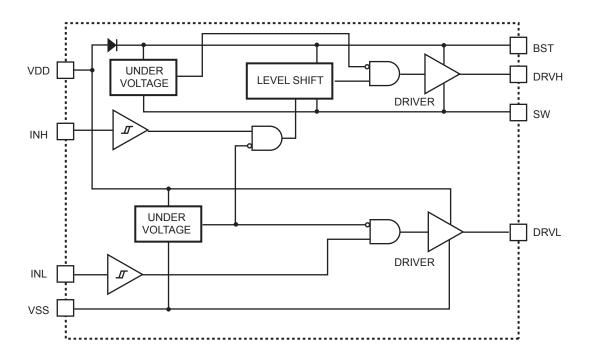


Figure 2: Function Block Diagram



APPLICATION

The input signals of INH and INL can be controlled independently. If both INH and INL control the high-side MOSFET and low-side MOSFET of the same bridge, then users must avoid shoot through by

setting sufficient dead time between INH and INL low, and vice versa. See Figure 3 below. Dead time is defined as the time interval between INH low and INL low.

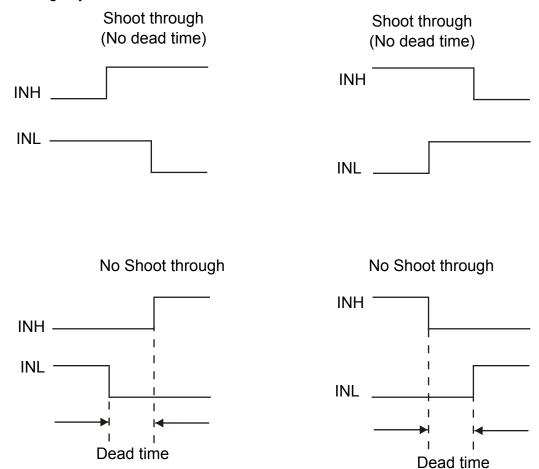


Figure 3: Shoot-Through Timing Diagram



REFERENCE DESIGN CIRCUITS

Half Bridge Converter

The MP1924 drives the MOSFETS with alternating signals (with dead time) in half-bridge converter topology. Therefore, from the PWM

controller drives INH and INL with alternating signals the input voltage can go up to 100V.

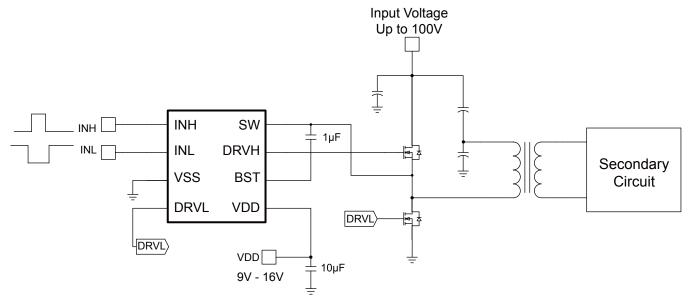


Figure 4: Half Bridge Converter

Two-Switch Forward Converter

In two-switch forward converter topology, both MOSFETs are turned on and off simultaneously. The input signal (INH and INL) comes from a PWM controller that senses the output voltage (and output current during current-mode control).

The Schottky diodes clamp the reverse swing of the power transformer and must be rated for the input voltage. The input voltage can go up to 100V.

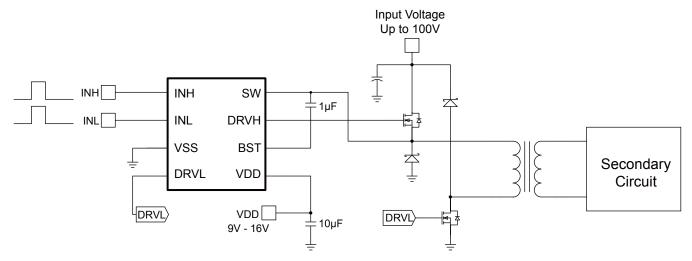


Figure 5: Two-Switch Forward Converter



Active-Clamp Forward Converter

In active-clamp forward converter topology, the MP1924 drives the MOSFETs with alternating signals. The high-side MOSFET, in conjunction with C_{reset} , is used to reset the power transformer in a lossless manner.

This topology lends itself well to run at duty cycles exceeding 50%. The device may not be able to run at 100V under this topology.

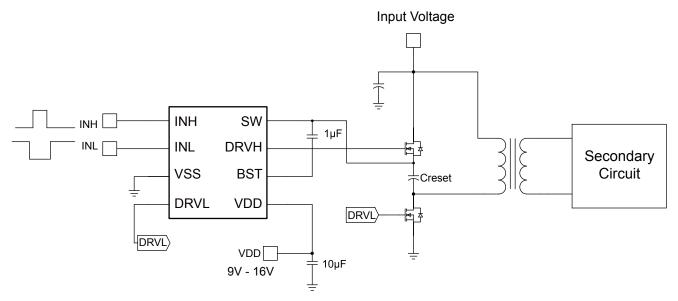
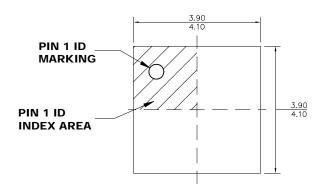


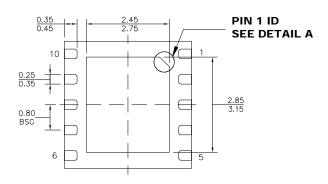
Figure 6 Active-Clamp Forward Converter



PACKAGE INFORMATION

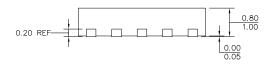
QFN-10 (4mm×4mm)



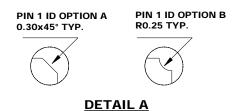


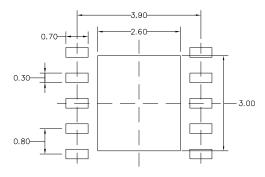
TOP VIEW

BOTTOM VIEW



SIDE VIEW





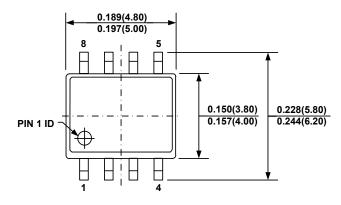
NOTE:

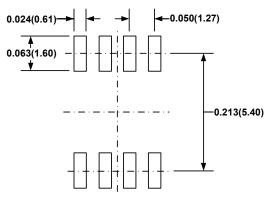
- 1) ALL DIMENSIONS ARE IN MILLIMETERS.
- 2) EXPOSED PADDLE SIZE DOES NOT INCLUDE MOLD FLASH.
- 3) LEAD COPLANARITY SHALL BE 0.10 MILLIMETERS MAX.
- 4) JEDEC REFERENCE IS MO-220.
- 5) DRAWING IS NOT TO SCALE.

RECOMMENDED LAND PATTERN



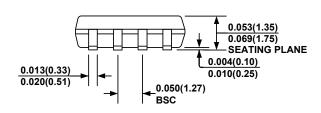
SOIC-8



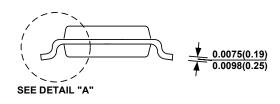


TOP VIEW

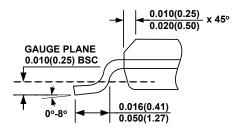
RECOMMENDED LAND PATTERN



FRONT VIEW



SIDE VIEW



DETAIL "A"

NOTE:

- 1) CONTROL DIMENSION IS IN INCHES. DIMENSION IN BRACKET IS IN MILLIMETERS.
- 2) PACKAGE LENGTH DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 3) PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS.
- 4) LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.004" INCHES MAX.
- 5) DRAWING CONFORMS TO JEDEC MS-012, VARIATION AA.
- 6) DRAWING IS NOT TO SCALE.

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